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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	49
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc56ap60l3befbr

Table 1. Device summary

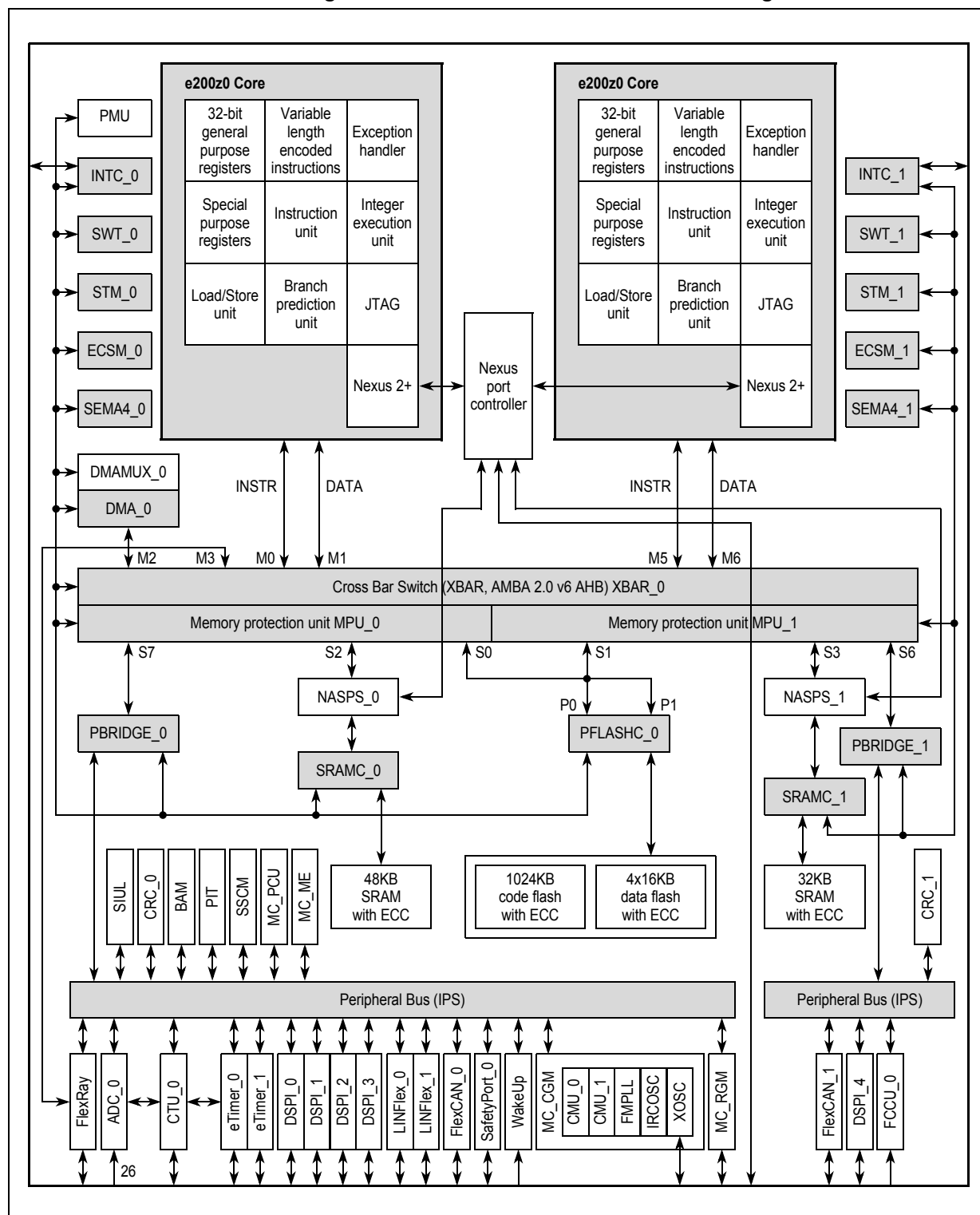
Package	Part number	
	768 KB Flash	1 MB Flash
LQFP144	SPC560P54L5 SPC56AP54L5	SPC560P60L5 SPC56AP60L5
LQFP100	SPC560P54L3 SPC56AP54L3	SPC560P60L3 SPC56AP60L3

	1.5.29	On-chip voltage regulator (VREG)	26
2		Package pinouts and signal descriptions	27
	2.1	Package pinouts	27
	2.2	Pin descriptions	29
	2.2.1	Power supply and reference voltage pins	29
	2.2.2	System pins	31
	2.2.3	Pin muxing	33
3		Electrical characteristics	48
	3.1	Introduction	48
	3.2	Parameter classification	48
	3.3	Absolute maximum ratings	49
	3.4	Recommended operating conditions	51
	3.5	Thermal characteristics	55
	3.5.1	General notes for specifications at maximum junction temperature	56
	3.6	Electromagnetic interference (EMI) characteristics	58
	3.7	Electrostatic discharge (ESD) characteristics	58
	3.8	Power management electrical characteristics	58
	3.8.1	Voltage regulator electrical characteristics	58
	3.8.2	Voltage monitor electrical characteristics	60
	3.9	Power Up/Down sequencing	61
	3.10	NVUSRO register	63
	3.10.1	NVUSRO[PAD3V5V] field description	63
	3.11	DC electrical characteristics	64
	3.11.1	DC electrical characteristics (5 V)	64
	3.11.2	DC electrical characteristics (3.3 V)	67
	3.11.3	I/O pad current specification	71
	3.12	Main oscillator electrical characteristics	72
	3.13	FMPLL electrical characteristics	73
	3.14	16 MHz RC oscillator electrical characteristics	74
	3.15	Analog-to-Digital converter (ADC) electrical characteristics	74
	3.15.1	Input impedance and ADC accuracy	75
	3.15.2	ADC conversion characteristics	80
	3.16	Flash memory electrical characteristics	81

List of tables

Table 1.	Device summary	2
Table 2.	SPC56xP54x/SPC56xP60x device comparison	8
Table 3.	SPC56xP54x/SPC56xP60x device configuration difference	10
Table 4.	SPC56xP54x/SPC56xP60x series block summary	12
Table 5.	Supply pins	29
Table 6.	System pins	31
Table 7.	Pin muxing	33
Table 8.	Parameter classifications	48
Table 9.	Absolute maximum ratings	49
Table 10.	Recommended operating conditions (5.0 V)	51
Table 11.	Recommended operating conditions (3.3 V)	52
Table 12.	Thermal characteristics for 144-pin LQFP	55
Table 13.	Thermal characteristics for 100-pin LQFP	56
Table 14.	EMI testing specifications	58
Table 15.	ESD ratings	58
Table 16.	Approved NPN ballast components	59
Table 17.	Voltage regulator electrical characteristics	60
Table 18.	Low voltage monitor electrical characteristics	61
Table 19.	PAD3V5V field description	63
Table 20.	DC electrical characteristics (5.0 V, NVUSRO[PAD3V5V]=0)	64
Table 21.	Supply current (5.0 V, NVUSRO[PAD3V5V]=0)	66
Table 22.	DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)	67
Table 23.	Supply current (3.3 V, NVUSRO[PAD3V5V]=1)	69
Table 24.	Peripherals supply current (5 V and 3.3 V)	70
Table 25.	I/O supply segment	71
Table 26.	I/O consumption	71
Table 27.	Main oscillator electrical characteristics (5.0 V, NVUSRO[PAD3V5V]=0)	72
Table 28.	Main oscillator electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)	72
Table 29.	Input clock characteristics	73
Table 30.	PLLMRFM electrical specifications ($V_{DDPLL} = 1.08\text{ V to }1.32\text{ V}$, $V_{SS} = V_{SSPLL} = 0\text{ V}$, $T_A = T_L$ to T_H)	73
Table 31.	16 MHz RC oscillator electrical characteristics	74
Table 32.	ADC conversion characteristics	80
Table 33.	Program and erase specifications	81
Table 34.	Flash memory module life	82
Table 35.	Flash read access timing	82
Table 36.	Output pin transition times	83
Table 37.	RESET electrical characteristics	85
Table 38.	JTAG pin AC electrical characteristics	86
Table 39.	Nexus debug port timing	88
Table 40.	External interrupt timing	90
Table 41.	DSPI timing	91
Table 42.	LQFP144 mechanical data	98
Table 43.	LQFP100 mechanical data	99
Table 44.	Document revision history	102

Figure 1. SPC56xP54x/SPC56xP60x block diagram



The default booting scheme is the one which uses the internal flash memory (an internal pull-down is used to select this mode). The alternate option allows the user to boot via FlexCAN or LINFlex (using the boot assist module software).

A censorship scheme is provided to protect the contents of the flash memory and offer increased security for the entire device.

A password mechanism is designed to grant the legitimate user access to the non-volatile memory.

1.5.16.1 Boot assist module (BAM)

The BAM is a block of read-only one-time programmed memory and is identical for all SPC56xP54x/SPC56xP60x devices that are based on the e200z0h core. The BAM program is executed every time the device is powered on if the alternate boot mode has been selected by the user.

The BAM provides the following features:

- Serial bootloading via FlexCAN or LINFlex.
- BAM can accept a password via the used serial communication channel to grant the legitimate user access to the non-volatile memory.

1.5.17 Error correction status module (ECSM)

The ECSM on this device features the following:

- Platform configuration and revision
- ECC error reporting for flash memory and SRAM
- ECC error injection for SRAM

The ECSM module is replicated for each processor.

1.5.18 FlexCAN

The FlexCAN module is a communication controller implementing the CAN protocol according to Bosch Specification version 2.0B. The CAN protocol was designed to be used primarily as a vehicle serial data bus, meeting the specific requirements of this field: real-time processing, reliable operation in the EMI environment of a vehicle, cost-effectiveness and required bandwidth. FlexCAN module contains 32 message buffers.

The FlexCAN module provides the following features:

- Full implementation of the CAN protocol specification, Version 2.0B
 - Standard data and remote frames
 - Extended data and remote frames
 - 0 to 8 bytes data length
 - Programmable bit rate as fast as 1 Mbit/s
- 32 message buffers of 0 to 8 bytes data length
- Each message buffer configurable as Rx or Tx, all supporting standard and extended messages
- Programmable loop-back mode supporting self-test operation
- 3 programmable mask registers

- Programmable transmit-first scheme: lowest ID or lowest buffer number
- Time stamp based on 16-bit free-running timer
- Global network time, synchronized by a specific message
- Maskable interrupts
- Independent of the transmission medium (an external transceiver is assumed)
- High immunity to EMI
- Short latency time due to an arbitration scheme for high-priority messages
- Transmit features
 - Supports configuration of multiple mailboxes to form message queues of scalable depth
 - Arbitration scheme according to message ID or message buffer number
 - Internal arbitration to guarantee no inner or outer priority inversion
 - Transmit abort procedure and notification
- Receive features
 - Individual programmable filters for each mailbox
 - 8 mailboxes configurable as a six-entry receive FIFO
 - 8 programmable acceptance filters for receive FIFO
- Programmable clock source
 - System clock
 - Direct oscillator clock to avoid PLL jitter

1.5.19 Safety port (FlexCAN)

The SPC56xP54x/SPC56xP60x MCU has a second CAN controller synthesized to run at high bit rates to be used as a safety port. The CAN module of the safety port provides the following features:

- Identical to the FlexCAN module
- Bit rate as fast as 7.5 Mb at 60 MHz CPU clock using direct connection between CAN modules (no physical transceiver required)
- 32 Message buffers of 0 to 8 bytes data length
- Can be used as a third independent CAN module

1.5.20 FlexRay

The FlexRay module provides the following features:

- Full implementation of FlexRay Protocol Specification 2.1
- 64 configurable message buffers can be handled
- Dual channel or single channel mode of operation, each as fast as 10 Mbit/s data rate
- Message buffers configurable as Tx, Rx or RxFIFO
- Message buffer size configurable
- Message filtering for all message buffers based on FrameID, cycle count and message ID
- Programmable acceptance filters for RxFIFO message buffers

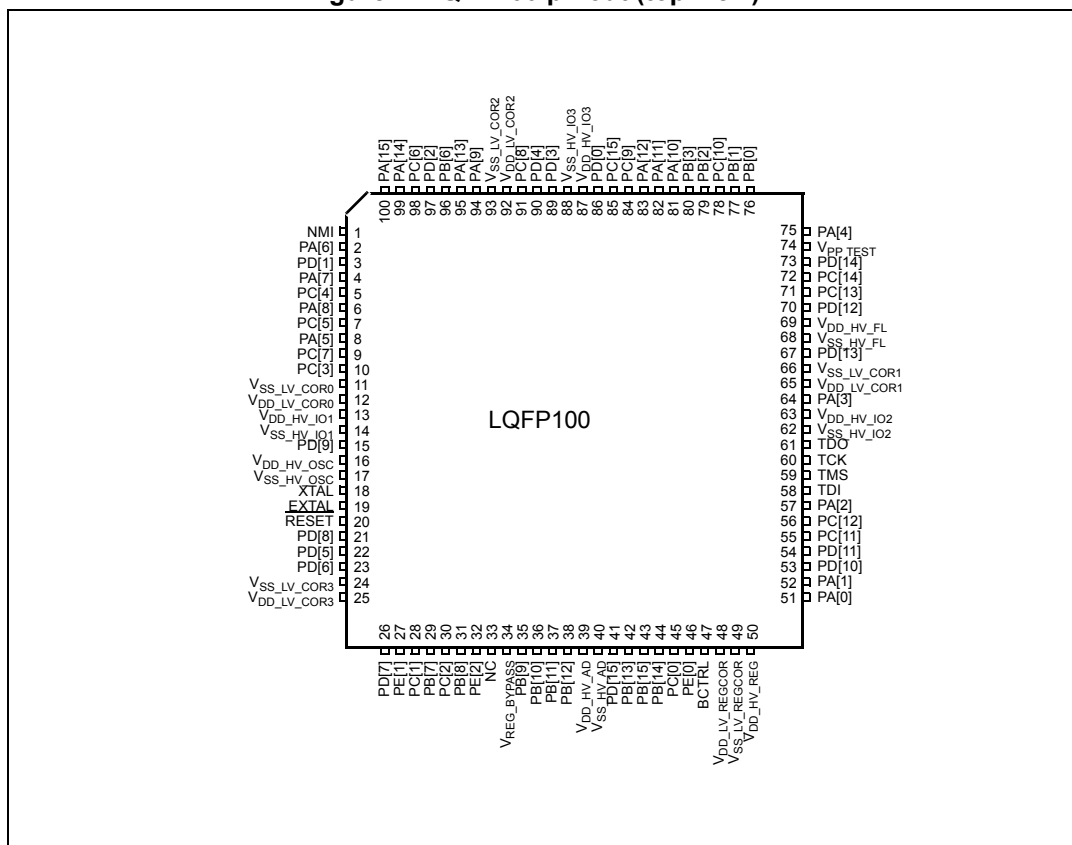
The DSPI modules provide these features:

- Full duplex, synchronous transfers
- Master or slave operation
- Programmable master bit rates
- Programmable clock polarity and phase
- End-of-transmission interrupt flag
- Programmable transfer baud rate
- Programmable data frames from 4 to 16 bits
- Up to 28 chip select lines available
 - 8 each on DSPI_0 and DSPI_1
 - 4 each on DSPI_2, DSPI_3, and DSPI_4
- 8 clock and transfer attributes registers
- Chip select strobe available as alternate function on one of the chip select pins for deglitching
- FIFOs for buffering up to 5 transfers on the transmit and receive side
- Queueing operation possible through use of the eDMA
- General purpose I/O functionality on pins when not used for SPI

1.5.23 eTimer

Two eTimer modules are provided, each with six 16-bit general purpose up/down timer/counter per module. The following features are implemented:

- Individual channel capability
 - Input capture trigger
 - Output compare
 - Double buffer (to capture rising edge and falling edge)
 - Separate prescaler for each counter
 - Selectable clock source
 - 0 % to 100% pulse measurement
 - Rotation direction flag (Quad decoder mode)
- Maximum count rate
 - Equals peripheral clock/2 — for external event counting
 - Equals peripheral clock — for internal clock counting
- Cascadeable counters
- Programmable count modulo
- Quadrature decode capabilities
- Counters can share available input pins
- Count once or repeatedly
- Preloadable counters
- Pins available as GPIO when timer functionality not in use

Figure 4. LQFP100 pinout (top view)^(d)

2.2 Pin descriptions

The following sections provide signal descriptions and related information about the functionality and configuration of the SPC56xP54x/SPC56xP60x devices.

2.2.1 Power supply and reference voltage pins

[Table 5](#) lists the power supply and reference voltage for the SPC56xP54x/SPC56xP60x devices.

Table 5. Supply pins

Supply		Pin		
Symbol	Description	LQFP 100	LQFP 144	LQFP 176 ⁽¹⁾
VREG control and power supply pins				
BCTRL	Voltage regulator external NPN Ballast base control pin	47	69	81

d. Availability of port pin alternate functions depends on product selection.

Table 7. Pin muxing⁽¹⁾ (continued)

Port pin	PCR No.	Alternate function ⁽²⁾ , (3)	Functions	Peripheral ⁽⁴⁾	I/O direction ⁽⁵⁾	Pad speed ⁽⁶⁾		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176 ⁽⁷⁾
C[7]	PCR[39]	ALT0	GPIO[39]	SIUL	I/O	Slow	Medium	9	15	23
		ALT1	—	—	—					
		ALT2	—	—	—					
		ALT3	DEBUG[7]	SSCM	—					
		—	SIN_0	DSPI_0	I					
		—	SIN_4	DSPI_4	I					
C[8]	PCR[40]	ALT0	GPIO[40]	SIUL	I/O	Slow	Medium	91	130	154
		ALT1	CS1_1	DSPI_1	O					
		ALT2	CS1_4	DSPI_4	O					
		ALT3	CS6_0	DSPI_0	O					
C[9]	PCR[41]	ALT0	GPIO[41]	SIUL	I/O	Slow	Medium	84	123	147
		ALT1	CS3_2	DSPI_2	O					
		ALT2	CS0_4	DSPI_4	I/O					
		ALT3	—	—	—					
C[10]	PCR[42]	ALT0	GPIO[42]	SIUL	I/O	Slow	Medium	78	111	135
		ALT1	CS2_2	DSPI_2	O					
		ALT2	CS2_4	DSPI_4	O					
		ALT3	—	—	—					
C[11]	PCR[43]	ALT0	GPIO[43]	SIUL	I/O	Slow	Medium	55	80	96
		ALT1	ETC[4]	eTimer_0	I/O					
		ALT2	CS2_2	DSPI_2	O					
		ALT3	CS0_3	DSPI_3	I/O					
C[12]	PCR[44]	ALT0	GPIO[44]	SIUL	I/O	Slow	Medium	56	82	100
		ALT1	ETC[5]	eTimer_0	I/O					
		ALT2	CS3_2	DSPI_2	O					
		ALT3	CS1_3	DSPI_3	O					
C[13]	PCR[45]	ALT0	GPIO[45]	SIUL	I/O	Slow	Medium	71	101	125
		ALT1	ETC[1]	eTimer_1	I/O					
		ALT2	—	—	—					
		ALT3	—	—	—					
		—	EXT_IN	CTU_0	I					
		—	RXD	FlexCAN_1	I					
C[14]	PCR[46]	ALT0	GPIO[46]	SIUL	I/O	Slow	Medium	72	103	127
		ALT1	ETC[2]	eTimer_1	I/O					
		ALT2	EXT_TGR	CTU_0	O					
		ALT3	TXD	FlexCAN_1	O					

Table 7. Pin muxing⁽¹⁾ (continued)

Port pin	PCR No.	Alternate function ⁽²⁾ , (3)	Functions	Peripheral ⁽⁴⁾	I/O direction ⁽⁵⁾	Pad speed ⁽⁶⁾		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176 ⁽⁷⁾
D[7]	PCR[55]	ALT0 ALT1 ALT2 ALT3 —	GPIO[55] CS3_1 — CS4_0 SIN_3	SIUL DSPI_1 — DSPI_0 DSPI_3	I/O O — O I	Slow	Medium	26	37	45
D[8]	PCR[56]	ALT0 ALT1 ALT2 ALT3	GPIO[56] CS2_1 RDY CS5_0	SIUL DSPI_1 nexus_0 DSPI_0	I/O O O O	Slow	Medium	21	32	40
D[9]	PCR[57]	ALT0 ALT1 ALT2 ALT3	GPIO[57] — TXD CS6_1	SIUL — LINFlex_1 DSPI_1	I/O — O O	Slow	Medium	15	26	34
D[10]	PCR[58]	ALT0 ALT1 ALT2 ALT3	GPIO[58] — CS0_3 —	SIUL — DSPI_3 —	I/O — I/O —	Slow	Medium	53	76	92
D[11]	PCR[59]	ALT0 ALT1 ALT2 ALT3	GPIO[59] — CS1_3 SCK_3	SIUL — DSPI_3 DSPI_3	I/O — O I/O	Slow	Medium	54	78	94
D[12]	PCR[60]	ALT0 ALT1 ALT2 ALT3 —	GPIO[60] — — CS7_1 RXD	SIUL — — DSPI_1 LINFlex_1	I/O — — O I	Slow	Medium	70	99	123
D[13]	PCR[61]	ALT0 ALT1 ALT2 ALT3	GPIO[61] — CS2_3 SOUT_3	SIUL — DSPI_3 DSPI_3	I/O — O O	Slow	Medium	67	95	119
D[14]	PCR[62]	ALT0 ALT1 ALT2 ALT3 —	GPIO[62] — CS3_3 — SIN_3	SIUL — DSPI_3 — DSPI_3	I/O — O — I	Slow	Medium	73	105	129
D[15]	PCR[63]	ALT0 ALT1 ALT2 ALT3 —	GPIO[63] — — — AN[20]	SIUL — — — ADC_0	Input Only	—	—	41	58	66

Table 7. Pin muxing⁽¹⁾ (continued)

Port pin	PCR No.	Alternate function ^{(2), (3)}	Functions	Peripheral (4)	I/O direction (5)	Pad speed ⁽⁶⁾		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176 ⁽⁷⁾
Port G										
G[0]	PCR[96]	ALT0 ALT1 ALT2 ALT3 —	GPIO[96] F[0] — — EIRQ[30]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	38	46
G[1]	PCR[97]	ALT0 ALT1 ALT2 ALT3 —	GPIO[97] F[1] — — EIRQ[31]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	141	173
G[2]	PCR[98]	ALT0 ALT1 ALT2 ALT3 —	GPIO[98] — — — SIN_4	SIUL — — — DSPI_4	I/O — — — I	Slow	Medium	—	102	126
G[3]	PCR[99]	ALT0 ALT1 ALT2 ALT3	GPIO[99] — SOUT_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	104	128
G[4]	PCR[100]	ALT0 ALT1 ALT2 ALT3	GPIO[100] — SCK_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	100	124
G[5]	PCR[101]	ALT0 ALT1 ALT2 ALT3	GPIO[101] — CS0_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	85	103
G[6]	PCR[102]	ALT0 ALT1 ALT2 ALT3	GPIO[102] — CS1_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	98	122
G[7]	PCR[103]	ALT0 ALT1 ALT2 ALT3	GPIO[103] — CS2_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	83	101

3.6 Electromagnetic interference (EMI) characteristics

Table 14. EMI testing specifications

Parameter	Symbol	Conditions	f_{OSC}/f_{BUS}	Frequency	Level (Max)	Unit
V_{RE_TEM}	Radiated emissions, electric field	$V_{DD} = 5\text{ V};$ $T_A = 25\text{ °C}$ 150 kHz–30 MHz RBW 9 kHz, Step Size 5 kHz	8 MHz crystal 64 MHz bus No PLL frequency modulation	150 kHz–150 MHz	18	dB μ V
				150–1000 MHz	12	
				IEC Level	M	—
		30 MHz–1 GHz RBW 120 kHz, Step Size 80 kHz	8 MHz crystal 64 MHz bus $\pm 2\%$ PLL frequency modulation	150 kHz–150 MHz	18	dB μ V
				150–1000 MHz	12	
				IEC Level	M	—

3.7 Electrostatic discharge (ESD) characteristics

Table 15. ESD ratings⁽¹⁾⁽²⁾

Symbol		Parameter	Conditions	Value	Unit
$V_{ESD(HBM)}$	SR	Electrostatic discharge (Human Body Model)	—	2000	V
$V_{ESD(CDM)}$	SR	Electrostatic discharge (Charged Device Model)	—	750 (corners)	V
				500 (other)	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

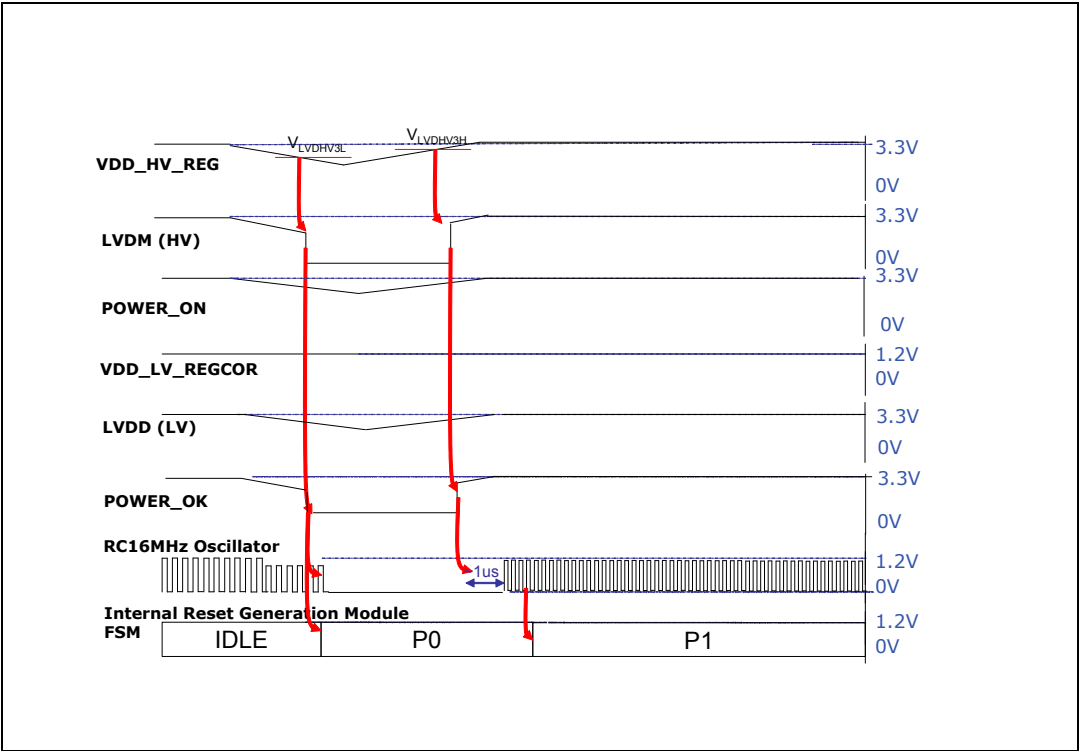
The internal voltage regulator requires an external NPN ballast to be connected as shown in [Figure 9](#). [Table 16](#) contains all approved NPN ballast components. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the $V_{DD_HV_REG}$, BCTRL and $V_{DD_LV_CORx}$ pins to less than L_{Reg} , see [Table 17](#).

Note: The voltage regulator output cannot be used to drive external circuits. Output pins are used only for decoupling capacitances.

$V_{DD_LV_COR}$ must be generated using internal regulator and external NPN transistor. It is not possible to provide $V_{DD_LV_COR}$ through external regulator.

For the SPC56xP54x/SPC56xP60x microcontroller, capacitors, with total values not below C_{DEC1} , should be placed between $V_{DD_LV_CORx}/V_{SS_LV_CORx}$ close to external ballast transistor emitter. 4 capacitors, with total values not below C_{DEC2} , should be placed close to microcontroller pins between each $V_{DD_LV_CORx}/V_{SS_LV_CORx}$ supply pairs and the

Figure 12. Brown-out typical sequence



3.10 NVUSRO register

Portions of the device configuration, such as high voltage supply, and watchdog enable/disable after reset are controlled via bit values in the non-volatile user options register (NVUSRO) register.

For a detailed description of the NVUSRO register, please refer to the device reference manual.

3.10.1 NVUSRO[PAD3V5V] field description

Table 19 shows how NVUSRO[PAD3V5V] controls the device configuration.

Table 19. PAD3V5V field description⁽¹⁾

Value ⁽²⁾	Description
0	High voltage supply is 5.0 V
1	High voltage supply is 3.3 V

1. See the device reference manual for more information on the NVUSRO register.
2. '1' is delivery value. It is part of shadow Flash, thus programmable by customer.

The DC electrical characteristics are dependent on the PAD3V5V bit value.

3.11 DC electrical characteristics

3.11.1 DC electrical characteristics (5 V)

Table 20 gives the DC electrical characteristics at 5 V ($4.5\text{ V} < V_{DD_HV_IOx} < 5.5\text{ V}$, $NVUSRO[PAD3V5V]=0$) as described in Figure 13.

Figure 13. I/O input DC electrical characteristics definition

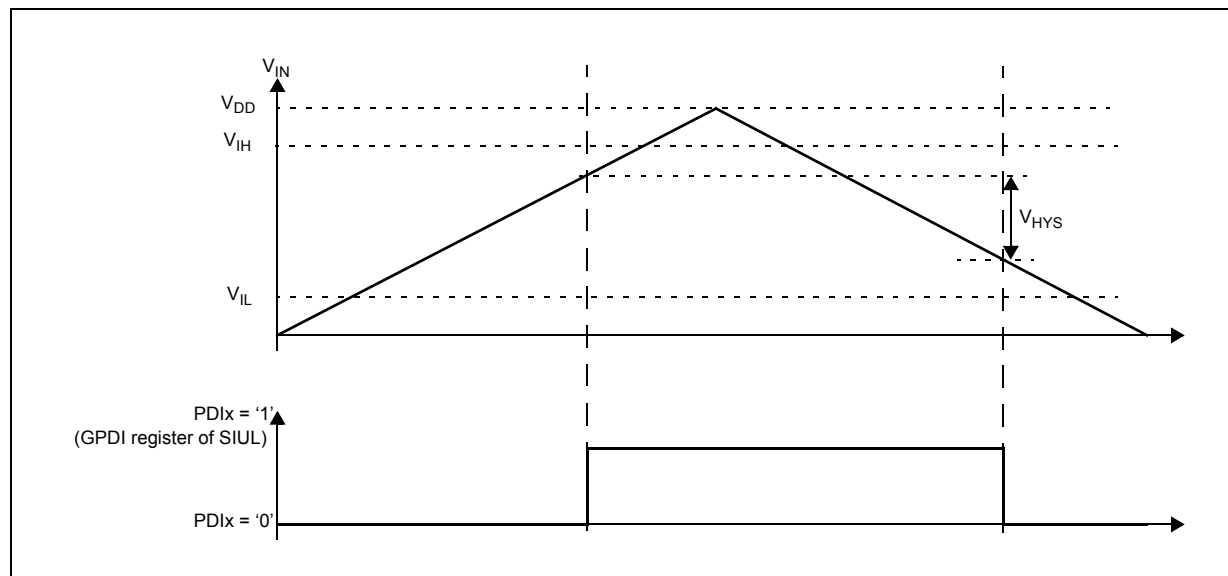


Table 20. DC electrical characteristics (5.0 V, $NVUSRO[PAD3V5V]=0$)

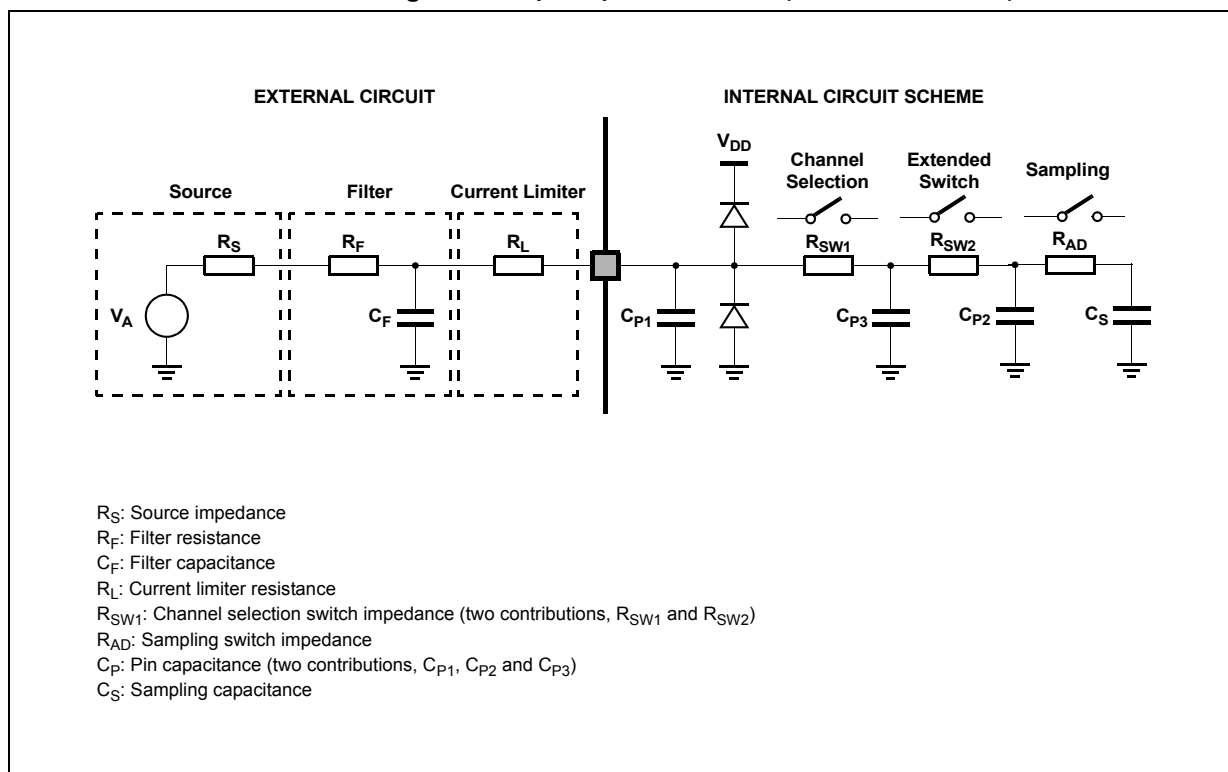
Symbol		Parameter	Conditions	Min	Max	Unit
V_{IL}	D	Minimum low level input voltage	—	$-0.1^{(1)}$	—	V
V_{IL}	P	Maximum level input voltage	—	—	$0.35 V_{DD_HV_IOx}$	V
V_{IH}	P	Minimum high level input voltage	—	$0.65 V_{DD_HV_IOx}$	—	V
V_{IH}	D	Maximum high level input voltage	—	—	$V_{DD_HV_IOx} + 0.1^{(1)}$	V
V_{HYS}	T	Schmitt trigger hysteresis	—	$0.1 V_{DD_HV_IOx}$	—	V
V_{OL_S}	P	Slow, low level output voltage	$I_{OL} = 3\text{ mA}$	—	$0.1 V_{DD_HV_IOx}$	V
V_{OH_S}	P	Slow, high level output voltage	$I_{OH} = -3\text{ mA}$	$0.8 V_{DD_HV_IOx}$	—	V
V_{OL_M}	P	Medium, low level output voltage	$I_{OL} = 3\text{ mA}$	—	$0.1 V_{DD_HV_IOx}$	V
V_{OH_M}	P	Medium, high level output voltage	$I_{OH} = -3\text{ mA}$	$0.8 V_{DD_HV_IOx}$	—	V
V_{OL_F}	P	Fast, low level output voltage	$I_{OL} = 3\text{ mA}$	—	$0.1 V_{DD_HV_IOx}$	V
V_{OH_F}	P	Fast, high level output voltage	$I_{OH} = -3\text{ mA}$	$0.8 V_{DD_HV_IOx}$	—	V
V_{OL_SYM}	P	Symmetric, low level output voltage	$I_{OL} = 3\text{ mA}$	—	$0.1 V_{DD_HV_IOx}$	V
V_{OH_SYM}	P	Symmetric, high level output voltage	$I_{OH} = -3\text{ mA}$	$0.8 V_{DD_HV_IOx}$	—	V

Table 24. Peripherals supply current (5 V and 3.3 V)⁽¹⁾

Symbol	Parameter	Conditions	Value		Unit
			Typ	Max	
$I_{DD_HV(CAN)}$	T CAN (FlexCAN) supply current on VDD_HV_REG	500 Kbyte/s Total (static + dynamic) consumption: – FlexCAN in loop-back mode – XTAL@ 8 MHz used as CAN engine clock source – Message sending period is 580 μ s	$21.6 * f_{periph}$	$28.1 * f_{periph}$	μ A
$I_{DD_HV(SCI)}$	T SCI (LINFlex) supply current on VDD_HV_REG	Total (static + dynamic) consumption: – LIN mode – Baudrate: 115.2 Kbyte/s	$10.8 * f_{periph}$	$14.1 * f_{periph}$	
$I_{DD_HV(SPI)}$	T SPI (DSPI) supply current on VDD_HV_REG	Ballast dynamic consumption (continuous communication): – Baudrate: 2 Mbit/s – Transmission every 8 μ s – Frame: 16 bits	$4.8 * f_{periph}$	$6.3 * f_{periph}$	
$I_{DD_HV(ADC)}$	T ADC supply current on VDD_HV_REG	VDD = 5.5 V Ballast dynamic consumption (continuous conversion)	$120 * f_{periph}$	$156 * f_{periph}$	mA
$I_{DD_HV_ADC(ADC)}$	T ADC supply current on VDD_HV_ADC	VDD = 5.5 V Analog dynamic consumption (continuous conversion)	$0.005 * f_{periph} + 2.8$	$0.007 * f_{periph} + 3.4$	
$I_{DD_HV(eTimer)}$	T eTimer supply current on VDD_HV_REG	PWM signals generation on all 1 channel @10kHz Dynamic consumption does not change varying the frequency	1.8	2.4	mA
$I_{DD_HV(FlexRay)}$	T FlexRay supply current on VDD_HV_REG	Static consumption	$4.2 * f_{periph}$	$5.5 * f_{periph}$	μ A

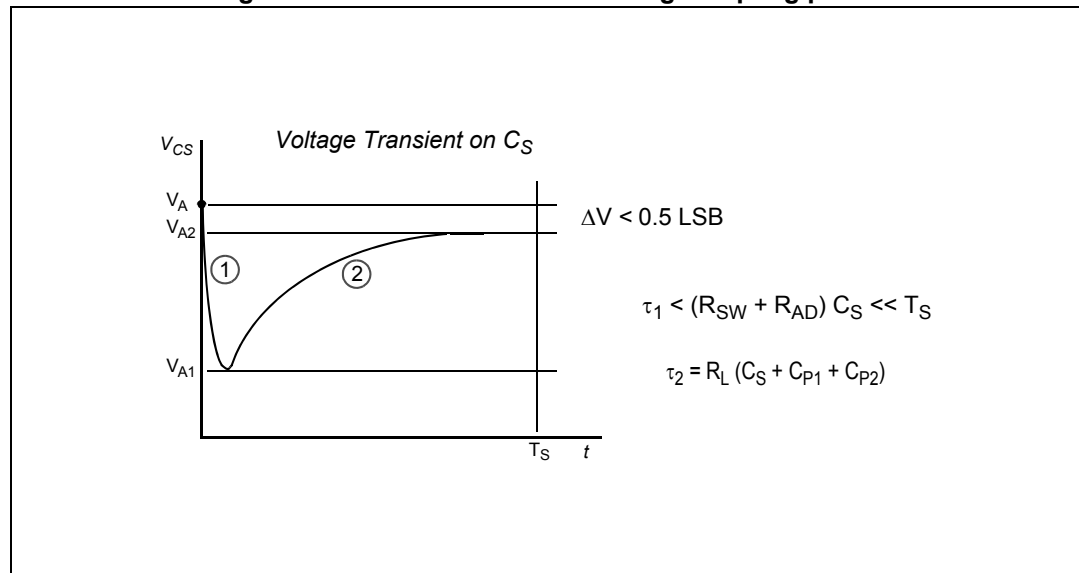
1. Operating conditions: f_{periph} = 8 MHz to 64 MHz

Figure 17. Input equivalent circuit (extended channels)



A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F , C_{P1} and C_{P2} are initially charged at the source voltage V_A (refer to the equivalent circuit reported in [Figure 16](#)): A charge sharing phenomenon is installed when the sampling phase is started (A/D switch close).

Figure 18. Transient behavior during sampling phase



In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \times \frac{C_P \times C_S}{C_P + C_S}$$

[Equation 5](#) can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \times C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S , determining a new value of the voltage V_{A1} on the capacitance according to [Equation 7](#):

Equation 7

$$V_{A1} \times (C_S + C_{P1} + C_{P2}) = V_A \times (C_{P1} + C_{P2})$$

- A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L : again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Equation 8

$$\tau_2 < R_L \times (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S , a constraint on R_L sizing is obtained:

Equation 9

$$8.5 \times \tau_2 = 8.5 \times R_L \times (C_S + C_{P1} + C_{P2}) < T_S$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1} , C_{P2} and C_S , then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1} . [Equation 10](#) must be respected (charge balance assuming now C_S already charged at V_{A1}):

Equation 10

$$V_{A2} \times (C_S + C_{P1} + C_{P2} + C_F) = V_A \times C_F + V_{A1} \times (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on

3.17 AC specifications

3.17.1 Pad AC specifications

Table 36. Output pin transition times

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
T_{tr}	CC	Output transition time output pin ⁽²⁾ SLOW configuration	$C_L = 25\text{ pF}$	—	—	50	ns
			$C_L = 50\text{ pF}$	—	—	100	
			$C_L = 100\text{ pF}$	—	—	125	
			$C_L = 25\text{ pF}$	—	—	40	
			$C_L = 50\text{ pF}$	—	—	50	
			$C_L = 100\text{ pF}$	—	—	75	
T_{tr}	CC	Output transition time output pin ⁽²⁾ MEDIUM configuration	$C_L = 25\text{ pF}$	—	—	10	ns
			$C_L = 50\text{ pF}$	—	—	20	
			$C_L = 100\text{ pF}$	—	—	40	
			$C_L = 25\text{ pF}$	—	—	12	
			$C_L = 50\text{ pF}$	—	—	25	
			$C_L = 100\text{ pF}$	—	—	40	
T_{tr}	CC	Output transition time output pin ⁽²⁾ FAST configuration	$C_L = 25\text{ pF}$	—	—	4	ns
			$C_L = 50\text{ pF}$	—	—	6	
			$C_L = 100\text{ pF}$	—	—	12	
			$C_L = 25\text{ pF}$	—	—	4	
			$C_L = 50\text{ pF}$	—	—	7	
			$C_L = 100\text{ pF}$	—	—	12	
$T_{sim}^{(3)}$	CC	Symmetric, same drive strength between N and P transistor	$V_{DD} = 5.0\text{ V} \pm 10\%$, $PAD3V5V = 0$	—	—	4	ns
			$V_{DD} = 3.3\text{ V} \pm 10\%$, $PAD3V5V = 1$	—	—	5	

1. $V_{DD} = 3.3\text{ V} \pm 10\%$ / $5.0\text{ V} \pm 10\%$, $T_A = -40\text{ }^{\circ}\text{C}$ to $T_{A\text{ MAX}}$, unless otherwise specified.

2. C_L includes device and package capacitances ($C_{PKG} < 5\text{ pF}$).

3. Transition timing of both positive and negative slopes will differ maximum 50 %.

3.18 AC timing characteristics

3.18.1 RESET pin characteristics

The SPC56xP54x/SPC56xP60x implements a dedicated bidirectional RESET pin.

Figure 32. DSPI classic SPI timing — slave, CPHA = 1

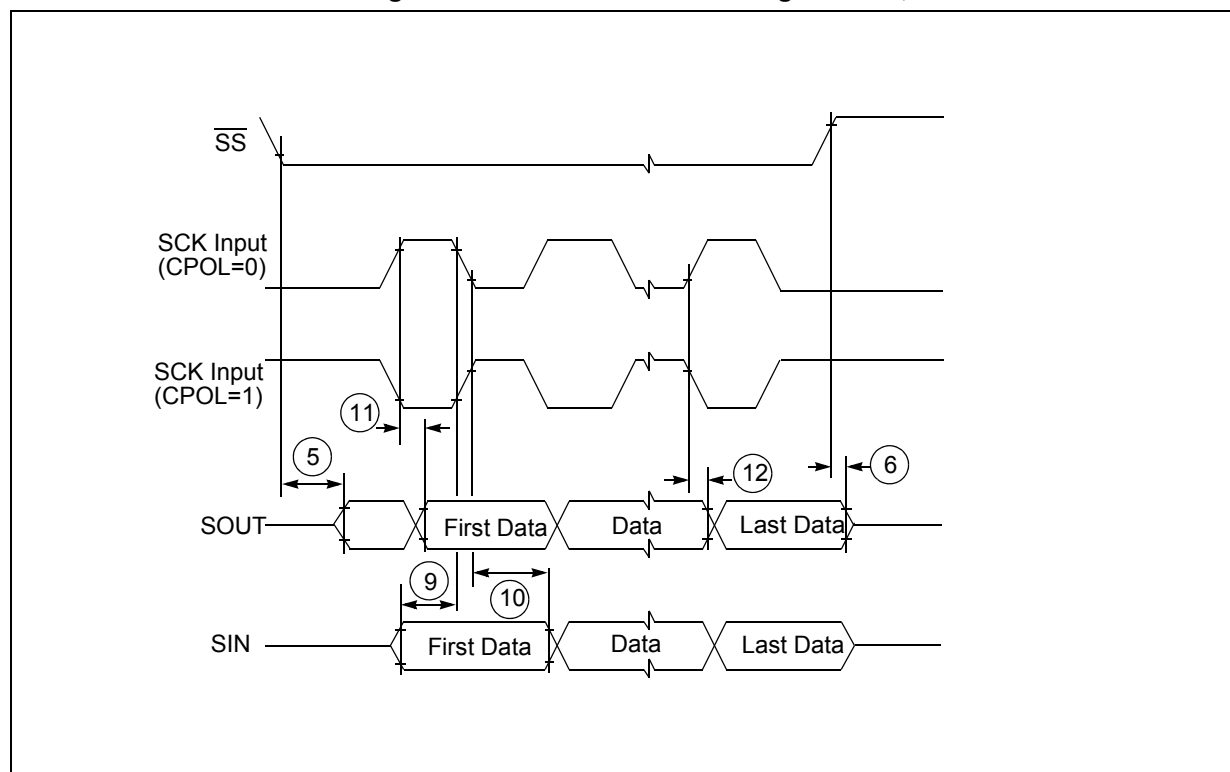


Figure 33. DSPI modified transfer format timing — master, CPHA = 0

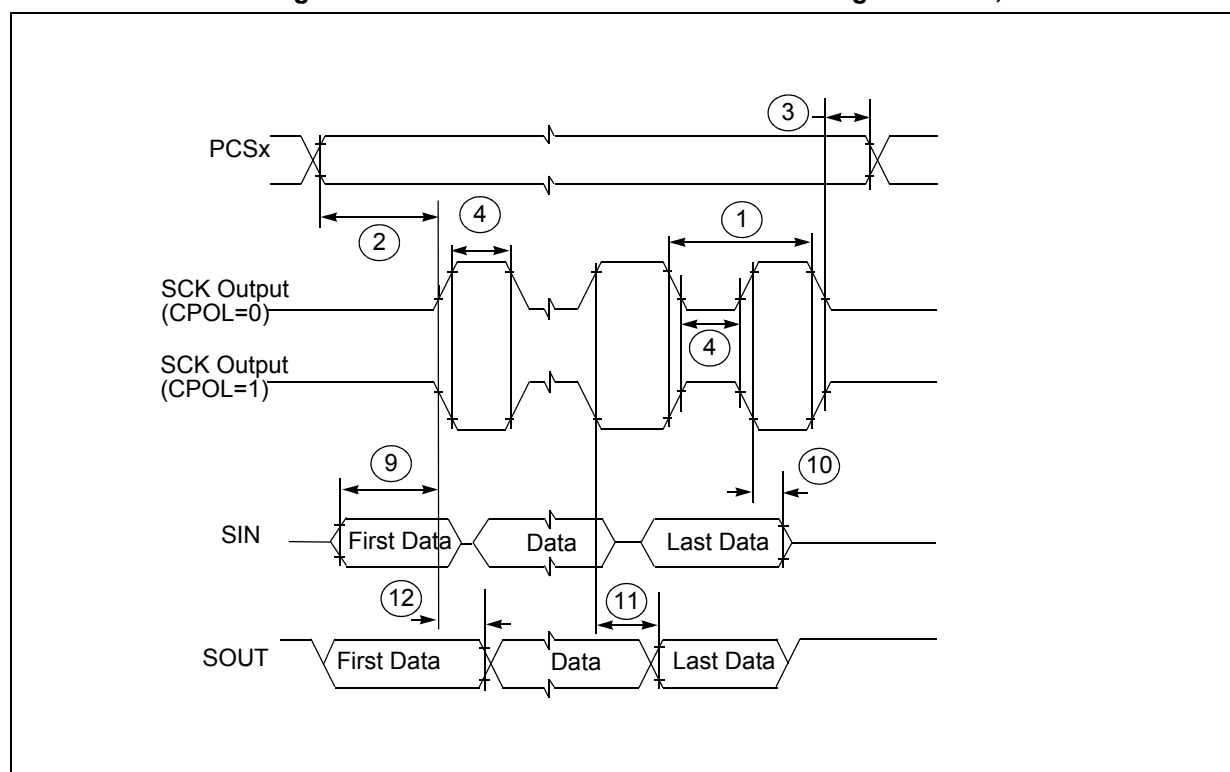


Figure 36. DSPI modified transfer format timing — slave, CPHA = 1

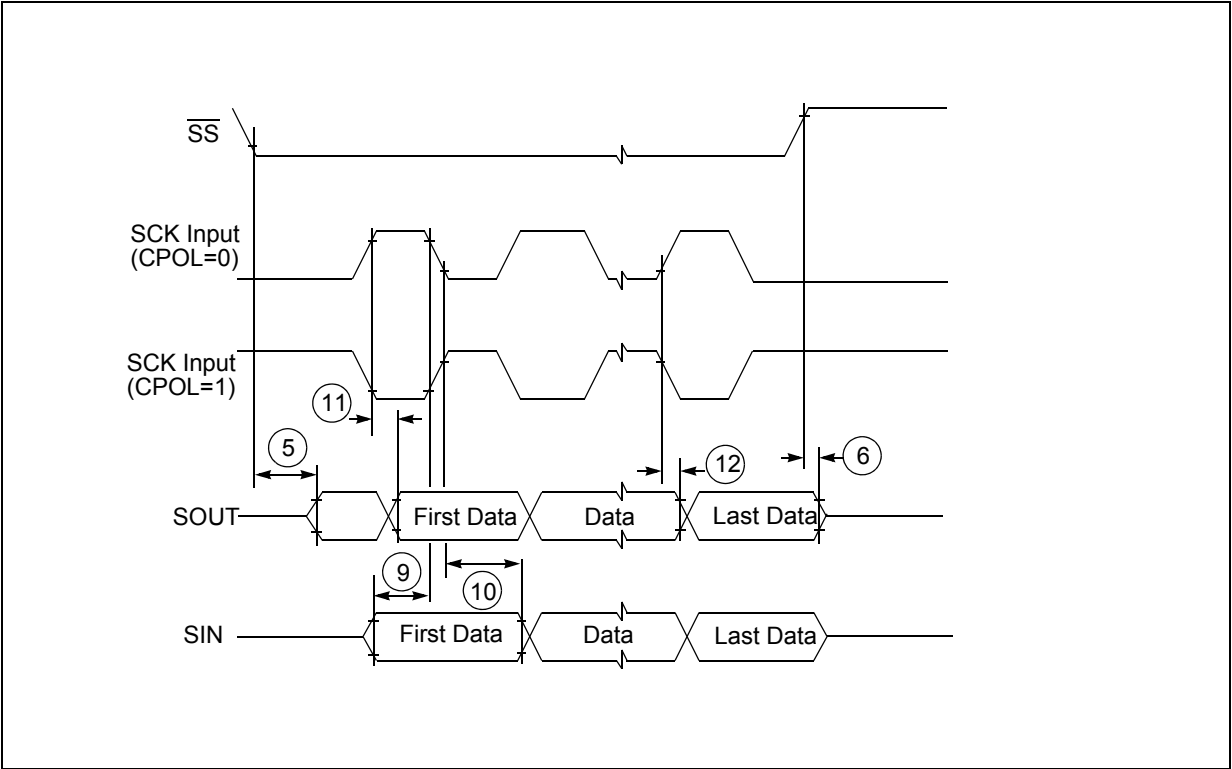


Figure 37. DSPI PCS strobe ($\overline{PCSS}$) timing

